

isc Silicon NPN Power Transistor
BU2508DW
DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 700V$ (Min)
- High Switching Speed
- Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

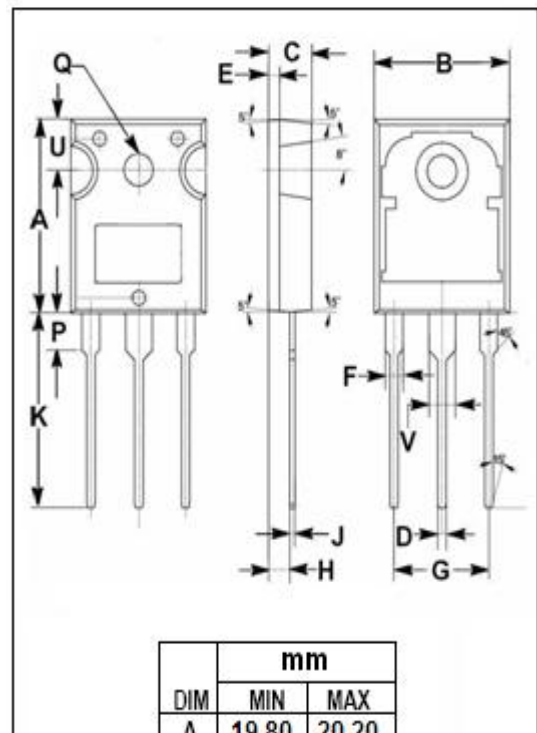
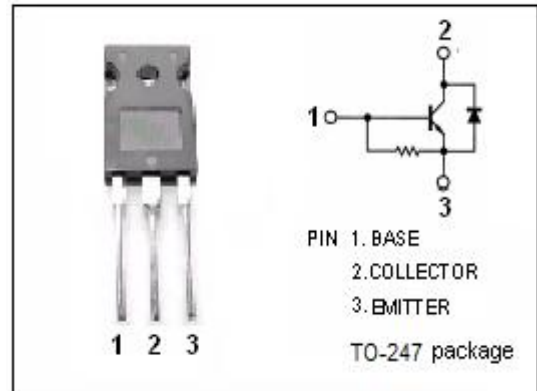
APPLICATIONS

- Designed for use in horizontal deflection circuits of color TV receivers.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector- Emitter Voltage ($V_{BE} = 0$)	1500	V
V_{CEO}	Collector-Emitter Voltage	700	V
V_{EBO}	Emitter-Base Voltage	7.5	V
I_C	Collector Current- Continuous	8	A
I_{CM}	Collector Current-Peak	15	A
I_B	Base Current- Continuous	4	A
I_{BM}	Base Current-Peak	6	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ C$	125	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.0	$^\circ C/W$



DIM	mm	
	MIN	MAX
A	19.80	20.20
B	15.40	15.80
C	4.90	5.10
D	0.90	1.10
E	1.40	1.60
F	1.90	2.10
G	10.80	11.00
H	2.40	2.60
J	0.50	0.70
K	19.50	20.50
P	3.90	4.10
Q	3.30	3.50
U	5.20	5.40
V	2.90	3.10

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ELECTRICAL CHARACTERISTICS

T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 50mA ; I _B = 0	700			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 600mA; I _C = 0	7.5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 4.5A; I _B = 1.12A			1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 4.5A; I _B = 1.7A			1.1	V
I _{CES}	Collector Cutoff Current	V _{CE} = 1500V ; V _{BE} = 0 V _{CE} = 1500V ; V _{BE} = 0; T _C =125°C			1.0 2.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 7.5V ; I _C = 0	140		390	mA
h _{FE-1}	DC Current Gain	I _C = 1A ; V _{CE} = 5V		13		
h _{FE-2}	DC Current Gain	I _C = 4.5A ; V _{CE} = 1V	4		7	
V _{ECF}	C-E Diode Forward Voltage	I _F = 4.5A			2.0	V
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} = 1MHz		80		pF

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